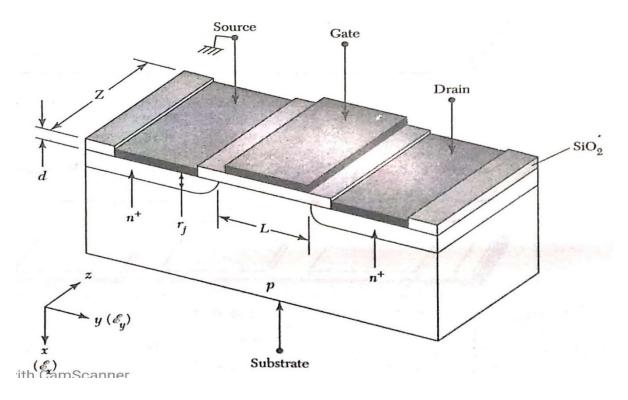
MOSFET

(METAL OXIDE SEMICONDUCTOR FIELD EFFECT TRANSISTOR)

Dr. MITHUN Kr. BHOWAL

BANGABASI MORNING COLLEGE

Structure:



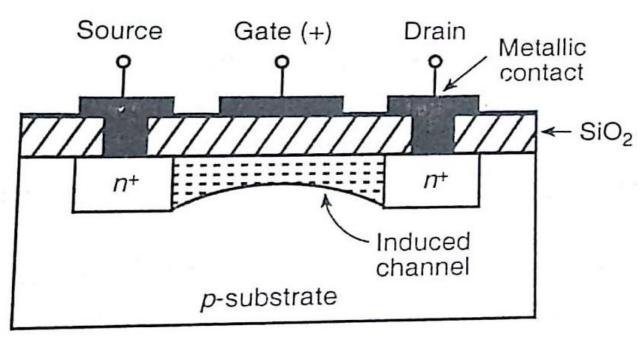


Fig. 9.7-1: Structure of *n*-channel enhancement MOSFET

Operation:

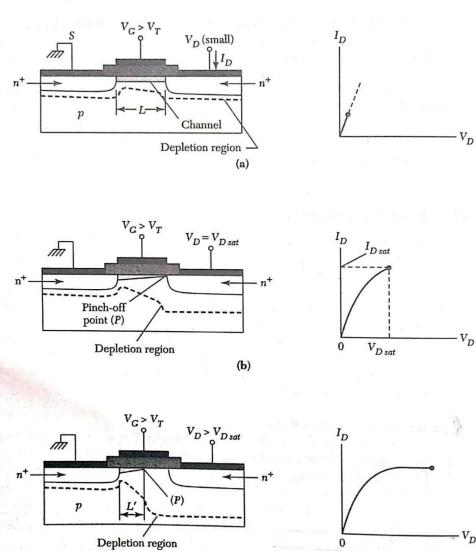


Fig. 15 Operations of the MOSFET and output *I-V* characteristics. (a) Low drain voltage. (b) Onset of saturation. Point P indicates the pinch-off point. (c) Beyond saturation.

(c)

Tyeps of MOSFET:

Туре	Cross section	Output characteristics
n-channel enhancement (normally off)	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	$\begin{array}{c c} I_D & V_C = 4V \\ \hline & 3 \\ \hline & 2 \\ \hline & 1 \\ \hline & V_D \\ \end{array}$
n-channel depletion (normally on)	$ \begin{array}{c c} & \pm \circ G \\ & I_D \downarrow \circ D \\ \hline & n^+ & p & n^+ \\ \hline & n\text{-Channel} \end{array} $	$V_G = 1V$ 0 -1 -2 V_D
p-channel enhancement (normally off)	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	$-V_{D} = -4V \qquad I_{D}$
p-channel depletion (normally on)	$ \begin{array}{c c} & \pm \circ G \\ & I_D \stackrel{\leftarrow}{\uparrow} \circ D \\ & p^+ & n & p^+ \\ \hline & p\text{-Channel} \end{array} $	$-V_{D} = -1V \qquad I_{D}$

Enhancement type & depletion type MOSFET:

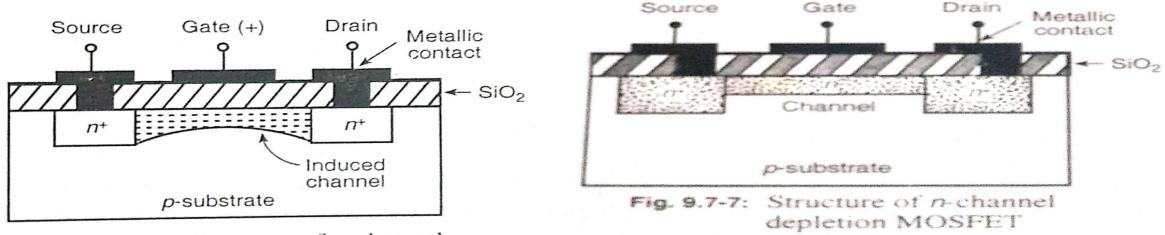


Fig. 9.7-1: Structure of n-channel enhancement MOSFET

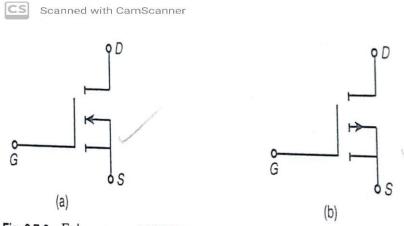
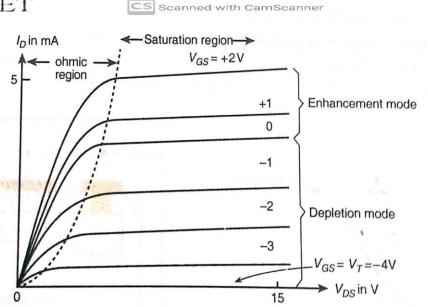


Fig. 9.7-2: Enhancement MOSFET symbols (a) n-channel (b) p-channel with Cam Coannar



Gate O Source O Source

Fig. 9.7-11: Depletion MOSFET symbols (a) n-channel (b) p-channel

Fig. 9.7-8: Drain characteristics of a typical n-channel depletion MOSFET

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Thank you